

## Description

The Si2302CDS-T1-E3 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

## **General Features**

 $V_{DS} = 20V I_D = 2.3 A$  $R_{DS(ON)} < 60m\Omega@ V_{GS} = 4.5V$ 

## Application

Battery protection Load switch Uninterruptible power supply

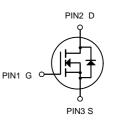
## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
Si2302CDS-T1-E3	SOT-23	HXY MOSFET	3000

## Absolute Maximum Ratings (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

Symbol	Parameter	Limit	Unit V	
VDS	Drain-Source Voltage	20		
V <sub>G</sub> s	Gate-Source Voltage	±12	V	
ID	Drain Current-Continuous	2.3	A	
Ідм	Drain Current-Pulsed (Note 1)	16	A	
PD	Maximum Power Dissipation	0.9	W	
Tj,Tstg	Operating Junction and Storage Temperature Range	-55 To 150	°C	
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	139	°C <b>/W</b>	





N-Channel MOSFET



N-Channel Enhancement Mode MOSFET

## Electrical Characteristics (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Мах	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA 20		22	-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V		-	1	μA
Gate-Body Leakage Current	lgss	V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	0.5	0.75	1.2	V
		$V_{GS}$ =2.5V, I <sub>D</sub> =2.0A	-	54	72	mΩ
Drain-Source On-State Resistance	Rds(on)	V <sub>GS</sub> =4.5V, I <sub>D</sub> =2.3A	-	48	60	mΩ
Forward Transconductance	gfs	V <sub>DS</sub> =5V,I <sub>D</sub> =2.3A	-	8	_	S
Input Capacitance	C <sub>lss</sub>		-	260	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =10V,V <sub>GS</sub> =0V,	-	48	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	27	-	PF
Turn-on Delay Time	td(on)		-	2.5	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =10V, R∟=3.3Ω	-	3.2	-	nS
Turn-Off Delay Time	td(off)	$V_{GS}$ =4.5V, $R_{GEN}$ =6 $\Omega$	-	21	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	3	-	nS
Total Gate Charge	Qg		-	2.9	5	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =10V,I <sub>D</sub> =2.3A,	-	0.4	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =4.5V	-	0.6	-	nC
Diode Forward Voltage (Note 3)	Vsd	V <sub>GS</sub> =0V,I <sub>S</sub> =2.3A	-	0.75	1.2	V
Diode Forward Current (Note 2)	ls		-	-	3.3	Α

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

**2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.

**3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4. Guaranteed by design, not subject to production



# Si2302CDS-T1-E3 N-Channel Enhancement Mode MOSFET

# **Typical Electrical and Thermal Characteristics**

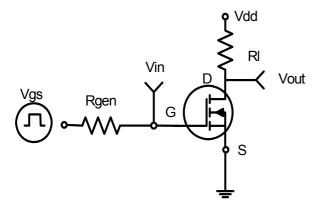
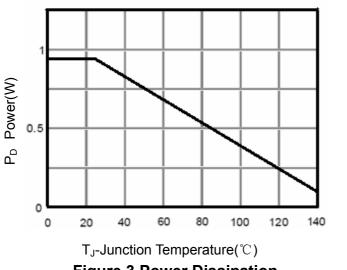
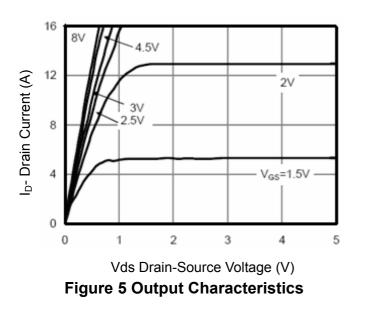
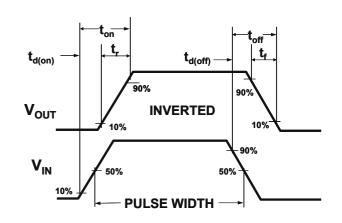


Figure 1:Switching Test Circuit

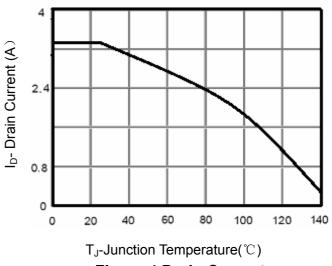


**Figure 3 Power Dissipation** 









**Figure 4 Drain Current** 

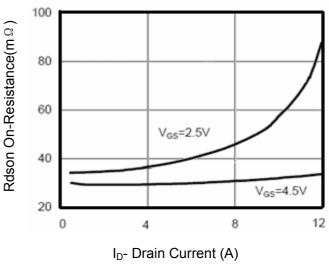
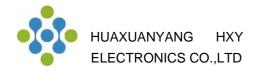
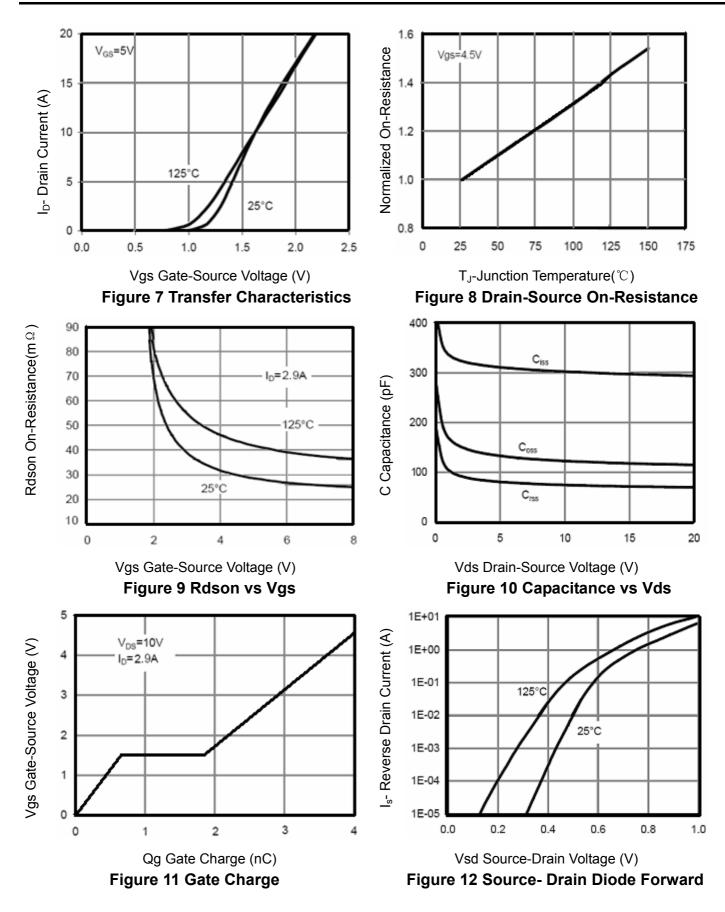


Figure 6 Drain-Source On-Resistance



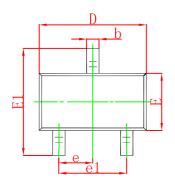
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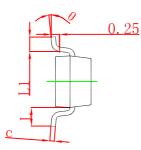
N-Channel Enhancement Mode MOSFET

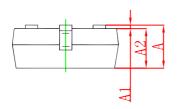




## **SOT-23 Package Outline Dimensions**

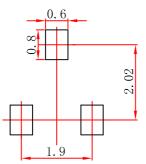






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
А	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
e	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# SOT-23 Suggested Pad Layout



Note: 1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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